Abstracts

Ka-Band Monolithic Broadband LNA Modules

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A set of broadband monolithic GaAs MESFET low noise amplifiers (LNAs) have been developed. These Ka-band amplifiers make use of state of the art sub .25 µm MESFET devices. Typical performance for a single stage LNA using a 75µm device is about 5 dB of gain with an average noise figure of 4.5 dB across the 26.5 to 40 GHz band. A two stage monolithic chip has 10 dB of gain with an average noise figure of 6 dB across the Ka-band.

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